

September 2006

# FAN73832 Half-Bridge Gate-Drive IC

#### **Features**

- Floating Channel for Bootstrap Operation to +600V
- Typically 350mA/650mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V<sub>S</sub> Swing to -9.8V for Signal Propagation at V<sub>DD</sub>=V<sub>BS</sub>=15V
- High-Side Output in Phase of IN Input Signal
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Canceling Circuit
- Internal 400nsec Minimum Dead-Time at R<sub>DT</sub>=20KΩ
- Programmable Turn-on Delay-Time Control (Dead-Time)

### **Applications**

- SMPS
- Motor Drive Inverter
- Fluorescent Lamp Ballast
- HID Ballast

### **Description**

The FAN73832 is a half-bridge, gate-drive IC with shutdown and programmable dead-time control functions for driving MOSFETs and IGBTs, operating up to +600V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side driver under high dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to  $V_S$ =-9.8V (typical) for  $V_{BS}$ =15V.

The UVLO circuits for both channels prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage.

Output drivers typically source/sink 350mA/650mA, respectively, which is suitable for all kinds of half- and full-bridge inverters.

8 SOP

8-DIP





### **Ordering Information**

Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method	
FAN73832M <sup>(1)</sup>	8-SOP			Tube	
FAN73832MX <sup>(1)</sup>	6-30F	Yes -40°C ~ 125°C	Yes	-40°C ~ 125°C	Tape & Reel
FAN73832N	8-DIP			Tube	

### Note:

1. These devices passed wave soldering test by JESD22A-111.

## **Typical Application Diagrams**

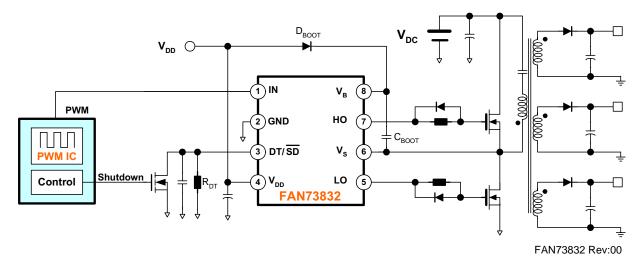


Figure 1. Application Circuit for Half-Bridge Switching Power Supply

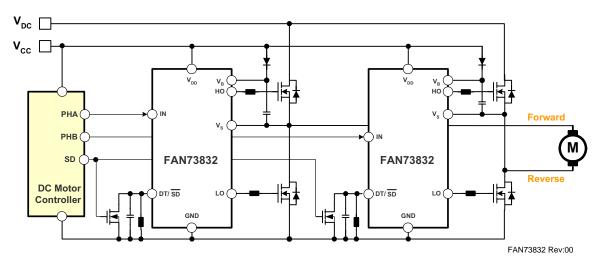


Figure 2. Application Circuit for Full-Bridge DC Motor Driver

## **Internal Block Diagram**

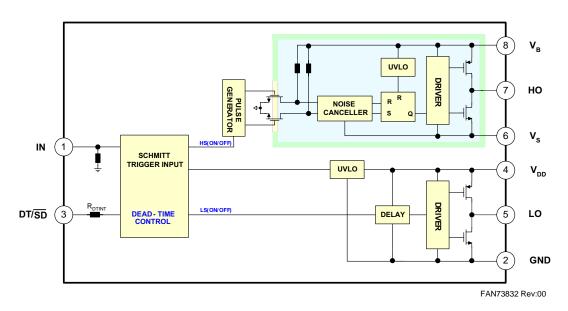


Figure 3. Functional Block Diagram of FAN73832

## **Pin Assignments**

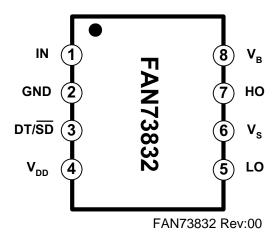


Figure 4. Pin Configuration (Top View)

### **Pin Definitions**

Pin#	Name	Description		
1	IN	Logic Input		
2	GND	Ground		
3	DT/SD	Dead-Time Control with External Resistor and Shutdown Function		
4	$V_{DD}$	Low-Side Supply Voltage		
5	LO	Low-Side Driver Output		
6	Vs	High-Side Floating Supply Return		
7	НО	High-Side Driver Output		
8	V <sub>B</sub>	High-Side Floating Supply		

### **Absolute Maximum Ratings**

The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table defines the conditions for actual device operation.  $T_A=25$ °C unless otherwise specified.

Symbol	Characteristics	Min.	Max.	Unit	
V <sub>S</sub>	High-side offset voltage		V <sub>B</sub> -25	V <sub>B</sub> +0.3	V
V <sub>B</sub>	High-side floating supply voltage		-0.3	625	V
V <sub>HO</sub>	High-side floating output voltage HO		V <sub>S</sub> -0.3	V <sub>B</sub> +0.3	V
$V_{DD}$	Low-side and logic-fixed supply voltage		-0.3	25	V
$V_{LO}$	Low-side output voltage LO		-0.3	V <sub>DD</sub> +0.3	V
V <sub>IN</sub>	Logic input voltage (IN)	-0.3	V <sub>DD</sub> +0.3	V	
V <sub>DT/SD</sub>	Dead-time and shutdown control voltage		-0.3	5.0	V
GND	Logic ground		V <sub>DD</sub> -25	V <sub>DD</sub> +0.3	V
dV <sub>S</sub> /dt	Allowable offset voltage slew rate			50	V/nsec
Pp <sup>(2)(3)(4)</sup>	Dawer discipation	8-SOP		0.625	W
P <sub>D</sub> ( //·// /	Power dissipation	8-DIP		1.25	
0	$\theta_{JA}$ Thermal resistance, junction-to-ambient 8-SOP 8-DIP			200	°C/M
θJA				100	°C/W
T <sub>J</sub>	Junction temperature			150	°C
T <sub>STG</sub>	Storage temperature			150	°C

#### Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 3. Refer to the following standards:
  - JESD51-2: Integral circuits thermal test method environmental conditions Natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages
- 4. Do not exceed P<sub>D</sub> under any circumstances.

### **Recommended Operating Conditions**

Symbol	Parameter	Condition	Min.	Max.	Unit
V <sub>B</sub>	High-side floating supply voltage		V <sub>S</sub> +15	V <sub>S</sub> +20	V
V <sub>S</sub>	High-side floating supply offset voltage		6-V <sub>DD</sub>	600	V
$V_{DD}$	Low-side supply voltage		15	20	V
V <sub>HO</sub>	High-side (HO) output voltage		V <sub>S</sub>	V <sub>B</sub>	V
V <sub>LO</sub>	Low-side (LO) output voltage		GND	$V_{DD}$	V
V <sub>IN</sub>	Logic input voltage (IN)		GND	$V_{DD}$	V
T <sub>A</sub>	Ambient temperature		-40	125	°C

### **Electrical Characteristics**

 $V_{BIAS} \ (V_{DD}, \ V_{BS}) = 15.0 V, \ R_{DT} = 20 K \Omega, \\ T_A = 25 ^{\circ} C, \ unless \ otherwise \ specified. \ The \ V_{IN} \ and \ I_{IN} \ parameters \ are \ referenced to GND. \ The \ V_O \ and \ I_O \ parameters \ are \ referenced to GND \ and \ V_S \ is \ applicable to HO \ and \ LO.$ 

Symbol	Characteristics	Test Condition	Min.	Тур.	Max.	Unit
SUPPLY CU	JRRENT SECTION					I
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	V <sub>IN</sub> =0V or 5V		35	90	
$I_{QDD}$	Quiescent V <sub>DD</sub> supply current	$V_{IN}$ =0V or 5V, $R_{DT}$ =20K $\Omega$		300	450	
I <sub>SD</sub> <sup>(4)</sup>	Shutdown supply current	DT/SD=GND		650	900	
I <sub>PBS</sub>	Operating V <sub>BS</sub> supply current	f <sub>IN</sub> =20kHz, rms value		400	700	μA
I <sub>PDD</sub>	Operating V <sub>DD</sub> supply current	f <sub>IN</sub> =20kHz, rms value		650	850	
I <sub>LK</sub>	Offset supply leakage current	V <sub>B</sub> =V <sub>S</sub> =600V			10	
POWER SU	IPPLY SECTION					I
V <sub>DDUV+</sub> V <sub>BSUV+</sub>	V <sub>DD</sub> and V <sub>BS</sub> supply under-voltage positive going threshold		10.7	11.6	12.5	V
V <sub>DDUV</sub> - V <sub>BSUV</sub> -	V <sub>DD</sub> and V <sub>BS</sub> supply under-voltage negative going threshold		10.0	10.8	11.6	V
V <sub>DDUVH</sub> V <sub>BSUVH</sub>	V <sub>DD</sub> supply under-voltage lockout hysteresis			0.8		V
DEAD-TIME	CONTROL SECTION					I
R <sub>DTINT</sub>	Internal dead-time setting resistance			20		ΚΩ
$V_{DT}$	Normal voltage at DT	R <sub>DT</sub> =20KΩ		3.0		V
GATE DRIV	ER OUTPUT SECTION					I
V <sub>OH</sub>	High-level output voltage, V <sub>BIAS</sub> -V <sub>O</sub>	I <sub>O</sub> =20mA			1.0	V
V <sub>OL</sub>	Low-level output voltage, V <sub>O</sub>				0.6	V
I <sub>O+</sub>	Output high short-circuit pulse current	V <sub>O</sub> =0V, V <sub>IN</sub> =5V with PW<10μs	250	350		mA
I <sub>O-</sub>	Output low short-circuit pulsed current	V <sub>O</sub> =15V, V <sub>IN</sub> =0V with PW<10µs	500	650		mA
V <sub>S</sub>	Allowable negative $V_{\rm S}$ pin voltage for IN signal propagation to HO			-9.8	-7.0	V
LOGIC INP	UT SECTION (INPUT and SHUTDOWN)					
V <sub>IH</sub>	Logic "1" input voltage		2.9			V
$V_{IL}$	Logic "0" input voltage				1.2	V
I <sub>IN+</sub>	Logic "1" input bias current	V <sub>IN</sub> =5V		50	100	μΑ
I <sub>IN-</sub>	Logic "0" input bias current	V <sub>IN</sub> =0V			2.0	μΑ
SD+	Shutdown "1" input voltage				1.2	V
SD-	Shutdown "0" input voltage		2.9			V
R <sub>PD</sub>	Input pull-down resistance			100		ΚΩ

### Note:

4. This parameter, although guaranteed, is not 100% tested in production.

## **Dynamic Electrical Characteristics**

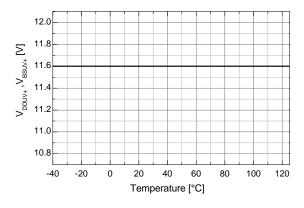
 $\rm V_{BIAS}~(V_{DD},~V_{BS}) = 15.0V,~V_{S} = GND,~C_{L} = 1000pF,~R_{DT} = 20K\Omega~and~T_{A} = 25^{\circ}C,~unless~otherwise~specified.$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t <sub>ON</sub>	Turn-on propagation delay	$V_S$ =0V, $R_{DT}$ =20K $\Omega$		580	730	
t <sub>OFF</sub>	Turn-off propagation delay	$V_S$ =0V, $R_{DT}$ =20K $\Omega$		180	230	
t <sub>R</sub>	Turn-on rise time	C <sub>L</sub> =1000pF		50	100	
t <sub>F</sub>	Turn-off fall time	C <sub>L</sub> =1000pF		30	80	
t <sub>SD</sub> <sup>(5)</sup>	Shutdown propagation delay			100	180	nsec
1 1111 1112 1 -	Dead-time LO OFF to HO ON & HO OFF to LO ON	R <sub>DT</sub> =20KΩ	300	400	500	
		R <sub>DT</sub> = 200KΩ	1.20	1.68	2.30	
DMT	Dead-time matching	$R_{DT} = 20K\Omega$		0	60	
	Dead-time matering	R <sub>DT</sub> =200KΩ		0	150	

### Note:

5. This parameter, although guaranteed, is not 100% tested in production.

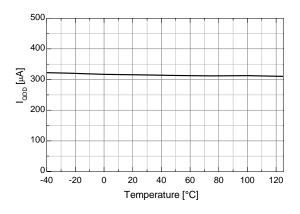
### **Typical Characteristics**



11.6 11.4 2 11.2 11.0 10.8 10.6 10.4 10.4 10.2 10.0 -40 -20 0 20 40 60 80 100 120 Temperature [°C]

Figure 5.  $V_{DD}/V_{DD}$  UVLO (+) vs. Temperature

Figure 6.  $V_{DD}/V_{BS}$  UVLO (-) vs. Temperature



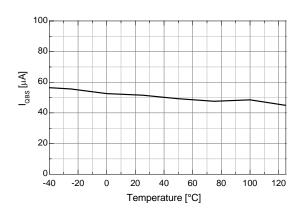
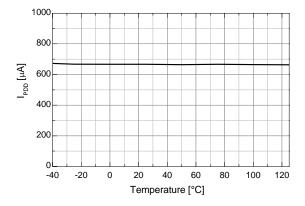


Figure 7.  $V_{DD}$  Quiescent Current vs. Temperature

Figure 8.  $V_{BS}$  Quiescent Current vs. Temperature



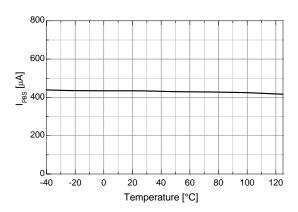
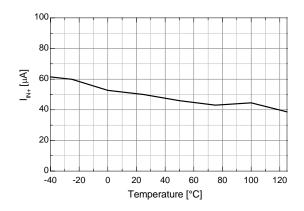


Figure 9.  $V_{DD}$  Operating Current vs. Temperature

Figure 10.  $V_{BS}$  Operating Current vs. Temperature

### **Typical Characteristics** (Continued)



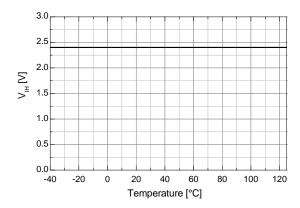
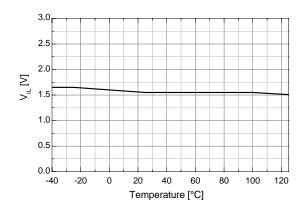


Figure 11. Logic Input Current vs. Temperature

Figure 12. Logic Input High Voltage vs. Temperature



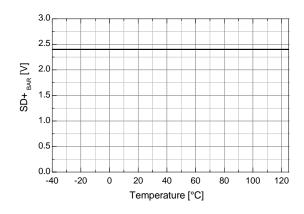
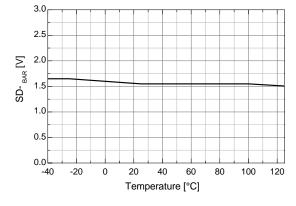


Figure 13. Logic Input Low Voltage vs. Temperature

Figure 14. SD Positive Threshold vs. Temperature



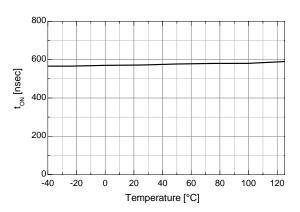
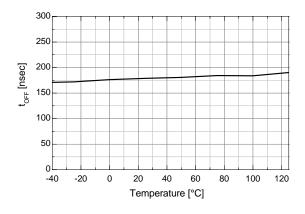


Figure 15. SD Negative Threshold vs. Temperature

Figure 16. Turn-on Delay Time vs. Temperature

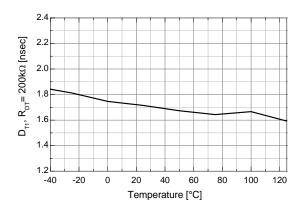
### Typical Characteristics (Continued)



350 450 20 350 300 -40 -20 0 20 40 60 80 100 120 Temperature [°C]

Figure 17. Turn-off Delay Time vs. Temperature

Figure 18. Dead Time (RDT=20k $\Omega$ ) vs. Temperature



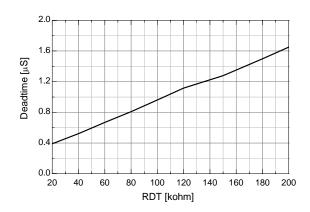


Figure 19. Dead Time (RDT=200k $\Omega$ ) vs. Temperature

Figure 20.  $R_{\rm DT}$  vs. Dead Time

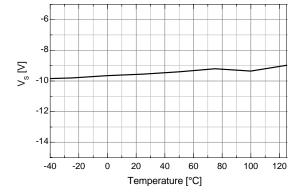


Figure 21. Allowable Negative  $V_S$  Voltage for Signal Propagation to High Side vs. Temperature

## **Switching Time Definitions**

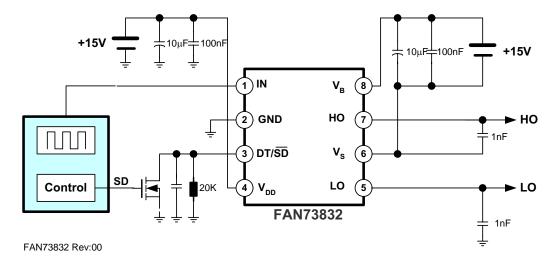


Figure 22. Switching Time Test Circuit

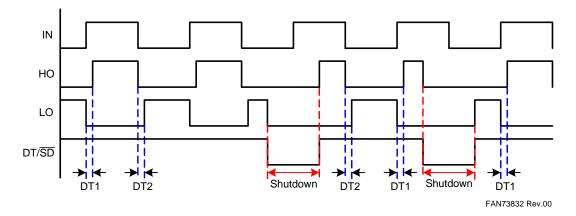


Figure 23. Input / Output Waveforms

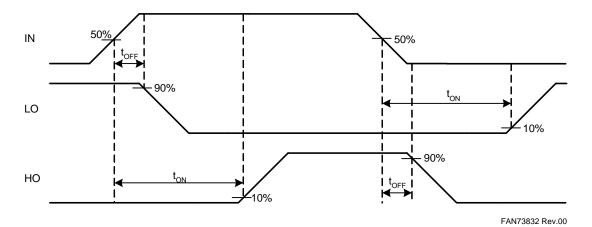


Figure 24. Switching Time Waveform Definitions

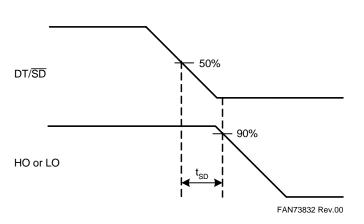


Figure 25. Shutdown Waveform Definition

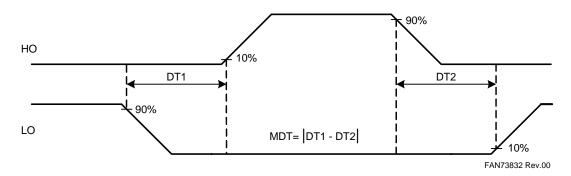


Figure 26. Dead-Time Control Waveform Definition

### **Typical Application Information**

### 1. Normal Operating Consideration

The FAN73832 is a single PWM input, half-bridge, gatedrive IC with programmable dead-time and shutdown functions.

The dead-time is set with a resistor ( $R_{DT}$ ) at the  $DT/\overline{SD}$  pin. The wide dead-time programming range provides the flexibility to optimize drive signal timing for a selection of switching devices (MOSFET or IGBT) and applications.

The turn-on time delay circuitry (Dead-Time) accommodates resistor values from  $20k\Omega$  to  $200k\Omega$  with a dead-time proportional to the  $R_{DT}$  resistance.

If the DT/SD pin voltage decreases below 1.2V in the normal operation, the IC enters shutdown mode.

The external dead-time setting resistor ( $R_{DT}$ ) is at least above 20K $\Omega$  for normal operation in typical applications.

#### 2. Under Voltage Lockout (UVLO)

The FAN73832 has an under-voltage lockout (UVLO) protection circuit for high- and low-side channels to prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage. The UVLO circuitry monitors the supply voltage ( $V_{DD}$ ) and bootstrap capacitor voltage ( $V_{BS}$ ) indepently.

### 3. Layout Consideration

For optimum performance of the high- and low-side gate drivers, considerations must be taken during printed circuit board (PCB) layout.

### 3.1 Supply Capacitors

If the output stages are able to quickly turn-on a switching device with a high value of current, the supply capacitors must be placed as close as possible to the device pins ( $V_{DD}$  and GND for the ground-tied supply,  $V_{B}$  and  $V_{S}$  for the floating supply) to minimize parasitic inductance and resistance.

### 3.2 Gate Drive Loop

Current loops behave like an antenna, able to receive and transmit noise. To reduce the noise coupling/emission and improve the power switch turn-on and off performances, gate drive loops must be reduced as much as possible.

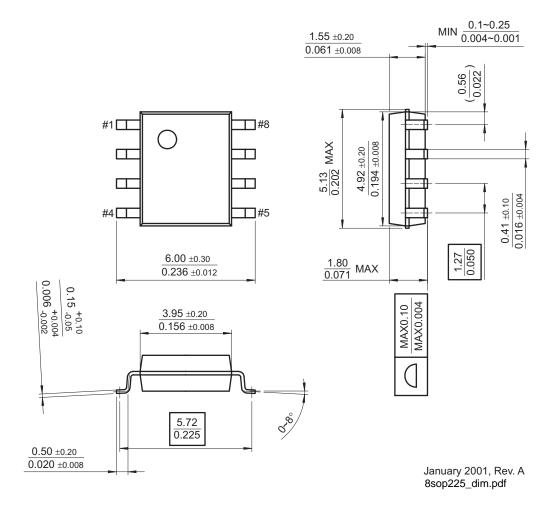
#### 3.3 Ground Plane

Ground plane must not be placed under or nearby the high-voltage floating side to minimize noise coupling.

## **Mechanical Dimensions**

### 8-SOP

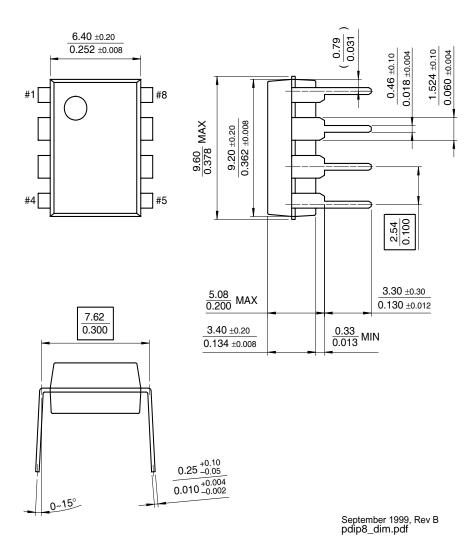
Dimensions are in millimeters (inches) unless otherwise noted.



### **Mechanical Dimensions** (Continued)

### 8-DIP

Dimensions are in millimeters (inches) unless otherwise noted.



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CoolFET™	<i>i-</i> Lo™	POP™	Stealth™	TinyPWM™
$CROSSVOLT^{r_{M}}$	ImpliedDisconnect™	Power247™	SuperFET™	TruTranslation™
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Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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